

At 25°C free air temperature:

Static Electrical Characteristics		NJ72 Process					Test Conditions
		Min	Typ	Max	Unit		
Gate Source Breakdown Voltage	$V_{(BR)GSS}$	- 25	- 40		V	$I_G = - 1 \mu A, V_{DS} = \emptyset V$	
Reverse Gate Leakage Current	$I_{GSS}$		- 10	- 100	pA	$V_{GS} = - 15V, V_{DS} = \emptyset V$	
Drain Saturation Current (Pulsed)	$I_{DSS}$	5		90	mA	$V_{DS} = 15V, V_{GS} = \emptyset V$	
Gate Source Cutoff Voltage	$V_{GS(OFF)}$	- 1		- 5.5	V	$V_{DS} = 15V, I_D = 1 nA$	

**Dynamic Electrical Characteristics**

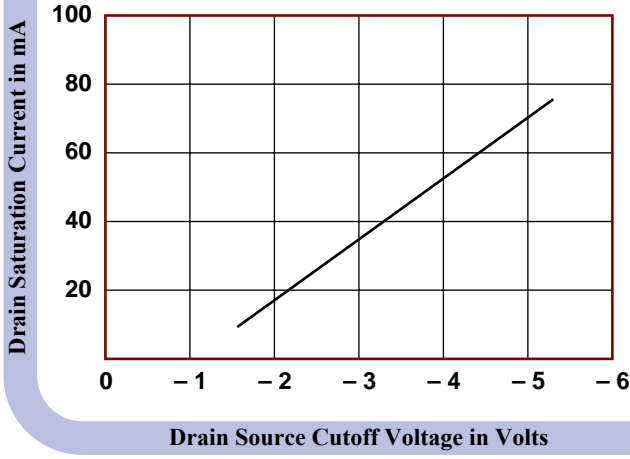
Forward Transconductance	$g_{fs}$		22		mS	$V_{DS} = 15V, V_{GS} = \emptyset V$	f = 1 kHz
Drain Source ON Resistance	$r_{ds(on)}$		40		$\Omega$	$I_D = 1 mA, V_{GS} = \emptyset V$	f = 1 kHz
Input Capacitance	$C_{iss}$		6.5		pF	$V_{DS} = \emptyset V, V_{GS} = - 10V$	f = 1 MHz
Feedback Capacitance	$C_{rss}$		2.5		pF	$V_{DS} = \emptyset V, V_{GS} = - 10V$	f = 1 MHz

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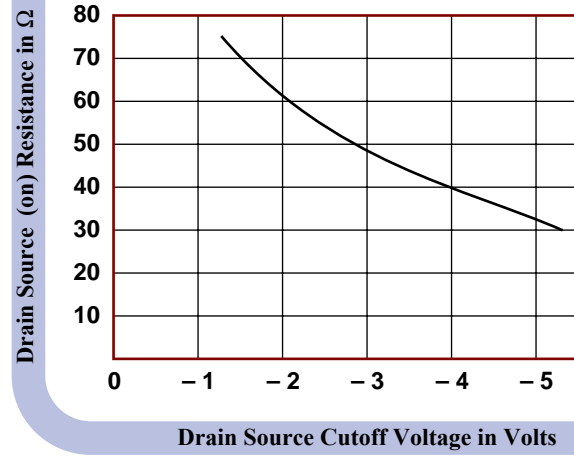
[www.interfet.com](http://www.interfet.com)



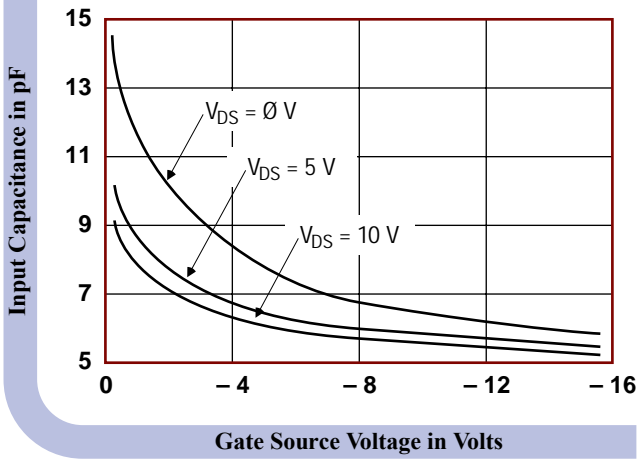
Drain Saturation Current as a Function of  $V_{GS(OFF)}$



$R_{ds}$  as a Function of  $V_{GS(OFF)}$



Input Capacitance as a Function of  $V_{GS}$



Feedback Capacitance as a Function of  $V_{GS}$

